2-Input AND Gate with **Open Drain Output**

The MC74VHC1G09 is an advanced high speed CMOS 2-input AND gate with open drain output fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The internal circuit is composed of three stages, including an open drain output which provides the capability to set output switching level. This allows the MC74VHC1G09 to be used to interface 5.0 V circuits to circuits of any voltage between V_{CC} and 7.0 V using an external resistor and power supply.

The MC74VHC1G09 input structure provides protection when voltages up to 7.0 V are applied, regardless of the supply voltage.

- High Speed: $t_{PD} = 4.3 \text{ ns}$ (Typ) at $V_{CC} = 5.0 \text{ V}$
- Low Internal Power Dissipation: $I_{CC} = 1 \mu A$ (Max) at $T_A = 25$ °C
- Power Down Protection Provided on Inputs
- Pin and Function Compatible with Other Standard Logic Families
- Chip Complexity: FETs = 62; Equivalent Gates = 16

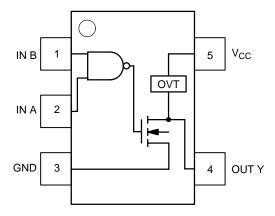


Figure 1. Pinout (Top View)



Figure 2. Logic Symbol



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MARKING DIAGRAMS

SC-88A / SOT-353/SC-70 **DF SUFFIX CASE 419A**



d = Date Code

TSOP-5/SOT-23/SC-59 **DT SUFFIX CASE 483**



d = Date Code

PIN ASSIGNMENT 1 IN B 2 IN A 3 **GND** 4 **OUT Y** 5

FUNCTION TABLE

 V_{CC}

Inp	uts	Output		
Α	В	Y		
L	L	L		
L	Н	L		
Н	L	L		
Н	Н	Z		

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

MAXIMUM RATINGS (Note 1)

Symbol		Characteristics	Value	Unit
V _{CC}	DC Supply Voltage		-0.5 to +7.0	V
V _{IN}	DC Input Voltage		-0.5 to +7.0	V
V _{OUT}	DC Output Voltage		-0.5 to 7.0	V
I _{IK}	Input Diode Current		-20	mA
I _{OK}	Output Diode Current		+20	mA
l _{OUT}	DC Output Current, per Pin		+25	mA
I _{CC}	DC Supply Current, V _{CC} and GN	ND	+50	mA
P _D	Power dissipation in still air	SC-88A, TSOP-5	200	mW
$\theta_{\sf JA}$	Thermal resistance	SC-88A, TSOP-5	333	°C/W
TL	Lead temperature, 1 mm from ca	ase for 10 s	260	°C
TJ	Junction temperature under bias		+150	°C
T _{stg}	Storage temperature		-65 to +150	°C
V _{ESD}	ESD Withstand Voltage	Human Body Model (Note 2) Machine Model (Note 3) Charged Device Model (Note 4)	> 2000 > 200 N/A	V
I _{Latch-Up}	Latch-Up Performance	Above V _{CC} and Below GND at 125°C (Note 5)	±500	mA

^{1.} Maximum Ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute-maximum-rated conditions is not implied. Functional operation should be restricted to the Recommended Operating Conditions.

- Tested to EIA/JESD22-A114-A 3. Tested to EIA/JESD22-A115-A
- Tested to JESD22-C101-A
- 5. Tested to EIA/JESD78

RECOMMENDED OPERATING CONDITIONS

Symbol	Characterist	Min	Max	Unit	
V _{CC}	DC Supply Voltage	2.0	5.5	V	
V _{IN}	DC Input Voltage	0.0	5.5	V	
V _{OUT}	DC Output Voltage		0.0	7.0	V
T _A	Operating Temperature Range		-55	+125	°C
t _r , t _f	Input Rise and Fall Time	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$ $V_{CC} = 5.0 \text{ V} \pm 0.5 \text{ V}$	0	100 20	ns/V

DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

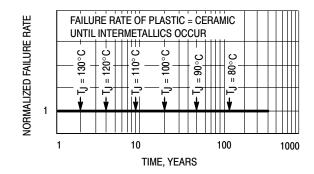


Figure 3. Failure Rate vs. Time **Junction Temperature**

DC ELECTRICAL CHARACTERISTICS

			V _{CC}	T _A = 25°C		T _A ≤	85°C	$-55 \le T_A \le 125$ °C			
Symbol	Parameter	Test Conditions	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
V _{IH}	Minimum High-Level Input Voltage		2.0 3.0 4.5 5.5	1.5 2.1 3.15 3.85			1.5 2.1 3.15 3.85		1.5 2.1 3.15 3.85		V
V _{IL}	Maximum Low–Level Input Voltage		2.0 3.0 4.5 5.5			0.5 0.9 1.35 1.65		0.5 0.9 1.35 1.65		0.5 0.9 1.35 1.65	V
V _{OH}	Minimum High-Level Output Voltage V _{IN} = V _{IH} or V _{IL}	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -50 \mu\text{A}$	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		1.9 2.9 4.4		V
		V _{IN} = V _{IH} or V _{IL} I _{OH} = -4 mA I _{OH} = -8 mA	3.0 4.5	2.58 3.94			2.48 3.80		2.34 3.66		V
V _{OL}	Maximum Low–Level Output Voltage V _{IN} = V _{IH} or V _{IL}	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50 \mu\text{A}$	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1		0.1 0.1 0.1	V
		$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 4 \text{ mA}$ $I_{OL} = 8 \text{ mA}$	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	V
I _{IN}	Maximum Input Leakage Current	V _{IN} = 5.5 V or GND	0 to 5.5			±0.1		±1.0		±1.0	μΑ
I _{CC}	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND	5.5			1.0		20		40	μΑ
I _{OPD}	Maximum Off-state Leakage Current	V _{OUT} = 5.5 V	0			0.25		2.5		5.0	μΑ

AC ELECTRICAL CHARACTERISTICS C_{load} = 50 pF, Input t_r = t_f = 3.0 ns

				Т	A = 25°C		T _A ≤ 85°C		$-55 \le T_A \le 125$ °C		
Symbol	Parameter	Test Condit	ions	Min	Тур	Max	Min	Max	Min	Max	Unit
t _{PZL}	Maximum Output Enable Time, Input A or B to Y	$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $R_L = R_I = 500 \Omega$	$C_L = 15 pF$ $C_L = 50 pF$		6.2 8.7	8.8 12.3		10.5 14.0		12.5 16.5	ns
	Input A or B to Y	$V_{CC} = 5.0 \pm 0.5 \text{ V}$ $R_L = R_I = 500 \Omega$	$C_L = 15 pF$ $C_L = 50 pF$		4.3 5.8	5.9 7.9		7.0 9.0		9.0 11.0	
t _{PLZ}	Maximum Output Disable Time	$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $R_L = R_I = 500 \Omega$	C _L = 50 pF		8.7	12.3		14.0		16.5	ns
		$V_{CC} = 5.0 \pm 0.5 \text{ V}$ $R_L = R_I = 500 \Omega$	C _L = 50 pF		5.8	7.9		9.0		11.0	
C _{IN}	Maximum Input Capacitance				6.0	10		10		10	pF

		Typical @ 25°C, V _{CC} = 5.0 V	
C _{PD}	Power Dissipation Capacitance (Note 6)	18	pF

^{6.} C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}. C_{PD} is used to determine the no–load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

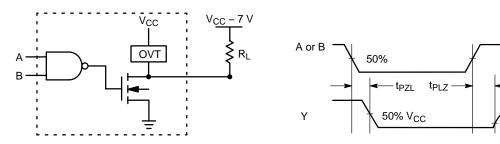


Figure 4. Output Voltage Mismatch Application

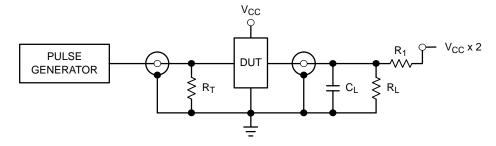
Figure 5. Switching Waveforms

 V_{CC}

· GND

HIGH IMPEDANCE

V_{OL} +0.3 V



C_L = 50 pF equivalent (Includes jig and probe capacitance)

 $R_L = R_1 = 500 \Omega$ or equivalent

 $R_T = Z_{OUT}$ of pulse generator (typically 50 Ω)

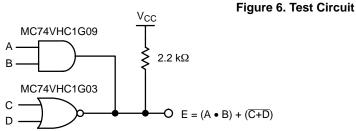


Figure 7. Complex Boolean Functions

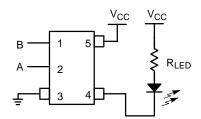
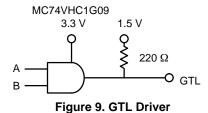


Figure 8. LED Driver



DEVICE ORDERING INFORMATION

	Device Nomenclature							
Device Order Number			Device Function	Package Suffix	Tape & Reel Suffix	Package Type (Name/SOT#/ Common Name)	Tape and Reel Size [†]	
MC74VHC1G09DFT1	МС	74	VHC1G	09	DF	T1	SC-88A / SOT-353 / SC-70	178 mm (7") 3000 Unit
MC74VHC1G09DFT2	МС	74	VHC1G	09	DF	T2	SC-88A / SOT-353 / SC-70	178 mm (7") 3000 Unit
MC74VHC1G09DTT1	МС	74	VHC1G	09	DT	T1	TSOP-5 / SOT-23 / SC-59	178 mm (7") 3000 Unit

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

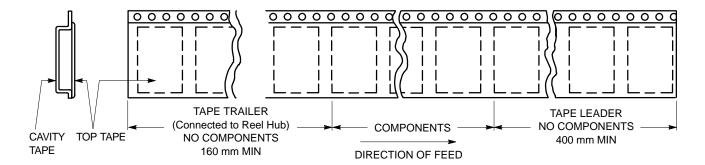


Figure 10. Tape Ends for Finished Goods

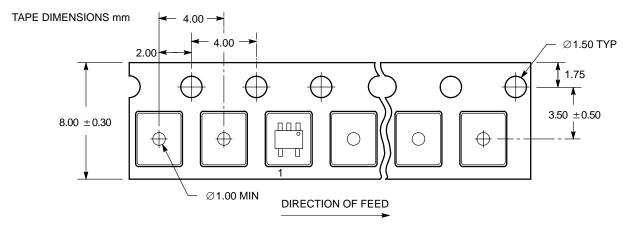


Figure 11. SC-70-5/SC-88A/SOT-353 DFT1 Reel Configuration/Orientation

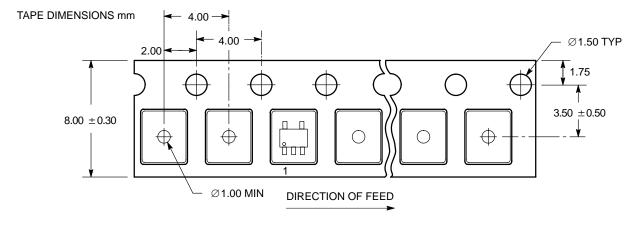


Figure 12. SC-70/SC-88A/SOT-353 DFT2 and SOT23-5/TSOP-5/SC59-5 DTT1 Reel Configuration/Orientation

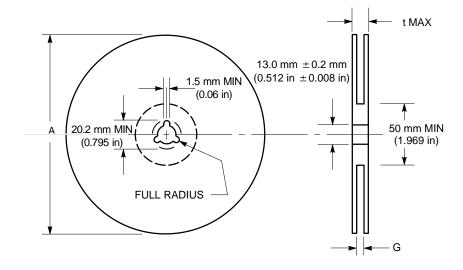


Figure 13. Reel Dimensions

REEL DIMENSIONS

Tape Size	T and R Suffix	A Max	G	t Max
8 mm	T1, T2	178 mm (7 in)	8.4 mm, + 1.5 mm, -0.0 (0.33 in + 0.059 in, -0.00)	14.4 mm (0.56 in)

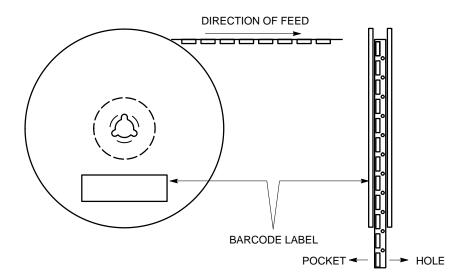
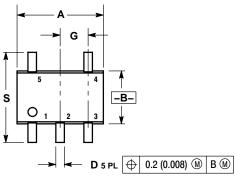


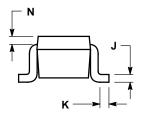
Figure 14. Reel Winding Direction

PACKAGE DIMENSIONS

SC70-5/SC-88A/SOT-353 **DF SUFFIX**

5-LEAD PACKAGE CASE 419A-02 **ISSUE G**





- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. 419A-01 OBSOLETE. NEW STANDARD
- 419A-02.
 DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	INC	HES	MILLIN	ETERS	
DIM	MIN	MAX	MIN	MAX	
Α	0.071	0.087	1.80	2.20	
В	0.045	0.053	1.15	1.35	
С	0.031	0.043	0.80	1.10	
D	0.004	0.012	0.10	0.30	
G	0.026	BSC	0.65 BSC		
Н		0.004		0.10	
J	0.004	0.010	0.10	0.25	
K	0.004	0.012	0.10	0.30	
N	0.008 REF		0.20 REF		
S	0.079	0.087	2 00	2 20	

SOLDERING FOOTPRINT*

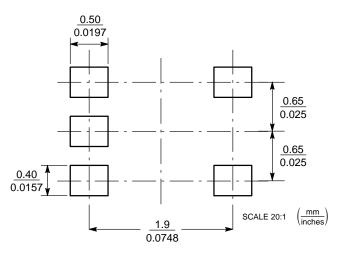


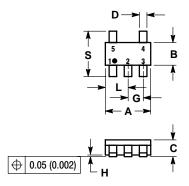
Figure 15. SC-88A/SC70-5/SOT-353

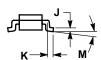
^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

SOT23-5/TSOP-5/SC59-5 **DT SUFFIX**

5-LEAD PACKAGE CASE 483-01 ISSUE C





NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- ANSI 114-3M, 1992.
 CONTROLLING DIMENSION: MILLIMETER.
 MAXIMUM LEAD THICKNESS INCLUDES
 LEAD FINISH THICKNESS. MINIMUM LEAD
 THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- A AND B DIMENSIONS DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	2.90	3.10	0.1142	0.1220	
В	1.30	1.70	0.0512	0.0669	
C	0.90	1.10	0.0354	0.0433	
D	0.25	0.50	0.0098	0.0197	
G	0.85	1.05	0.0335	0.0413	
Н	0.013	0.100	0.0005	0.0040	
۲	0.10	0.26	0.0040	0.0102	
Κ	0.20	0.60	0.0079	0.0236	
L	1.25	1.55	0.0493	0.0610	
М	0	10	0	10	
S	2.50	3.00	$0.098\overline{5}$	0.1181	

SOLDERING FOOTPRINT*

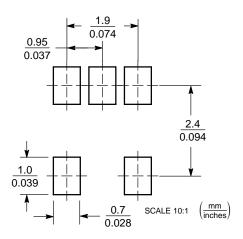


Figure 16. THIN SOT23-5/TSOP-5/SC59-5

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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